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N-Channel 100 V (D-S) Super Junction MOSFET

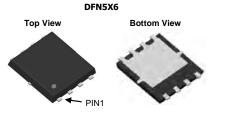
PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
100	6.3 at V _{GS} = 10 V	105	37 nC			

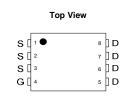
FEATURES

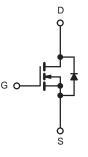
- **DT-SJ Power MOSFET**
- Very low on-resistance
- 100 % Rg and UIS Tested
- Fast switching •

APPLICATIONS

- Power Management
- Motor Drivers ٠
- **DC-DC** Converters ٠







N-Channel MOSFET

ORDERING INFORMATION						
Part Number	Package Type	Form	# of Pins	MSL	Qty(pcs)	
DTQ6080N10SJ	DFN5X6-8L	Reel	8	3	5000	

ABSOLUTE MAXIMUM RATINGS	S (T _A = 25 °C, unle	ess otherwise no	oted)	
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage		V _{GS}		
Continuous Drain Current (T ₁ = 150 °C)	T _C = 25 °C	1	105	
Continuous Drain Current $(1) = 150^{\circ}$ C)	T _C = 100 °C	I _D	65	A
Pulsed Drain Current (t = 300 µs)		I _{DM}	400	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	64	
ingle Pulse Avalanche Energy		E _{AS}	205	mJ
	T _C = 25 °C		125	
Maximum Power Dissipation	T _C = 100 °C	PD	80	w
	T _A = 25 °C	' D	2.1 ^{b, c}	
	T _A = 100 °C		2.84 ^{b, c}	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	-55 to 150	つ ∘	
Soldering Recommendations (Peak Temperature		260	Ŭ	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	40	60	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	0.8	1	0/11	

Notes:

a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.

- d. The DFN5X6 is a leadless package. The end of the lead terminal is exposed copper
- (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 70 °C/W.



COMPLIANT

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V_{DS} $V_{GS} = 0 V$, $I_D = 250 \mu A$		-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},\ I_{D}=250\ \mu A$	1	-	3	v	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA	
		$V_{DS} = 100 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$		-	10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \geq 10~V,~V_{GS} = 10~V$	105	-	-	А	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	-	6.3	8.0	mΩ	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 15 A		65	-	S	
Dynamic ^b			-	•	•		
Input Capacitance	C _{iss}		-	1880	-	pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 50 V, f = 1MHz	-	931	-		
Reverse Transfer Capacitance	C _{rss}		-	21	-		
Total Gate Charge ^c	Qg		-	37	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	-	4.2	-		
Gate-Drain Charge ^c	Q _{gd}		-	8.5	-		
Gate Resistance	R _g	f = 1 MHz	-	2	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	15	-	– ns	
Rise Time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_{g} = 6 \Omega$	-	33	-		
Turn-Off Delay Time ^c	t _{d(off)}	$I_{\rm D} = 15$ A, $V_{\rm GEN} = 10$ V,	-	61	-		
Fall Time ^c	t _f		-	28	-	1	
Drain-Source Body Diode Ratings and	nd Characteris	stics ^b (T _C = 25 °C)	·		·		
Continuous Source Current	I _S	T _C = 25 °C	-	-	105	А	
Pulsed Source Current	I _{SM}		-	-	400	А	
Forward Voltage ^a	V _{SD}	$I_F = 1 \text{ A}, V_{GS} = 0 \text{ V}$	-	-	1	V	
Reverse Recovery Time	t _{rr}	L = 15 A di/dt = 100 A/···	-	220	-	ns	
Reverse Recovery Charge	Q _{rr}	I _F = 15 A, di/dt = 100 A/μs	-	480	-	nC	

Notes

a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%.$

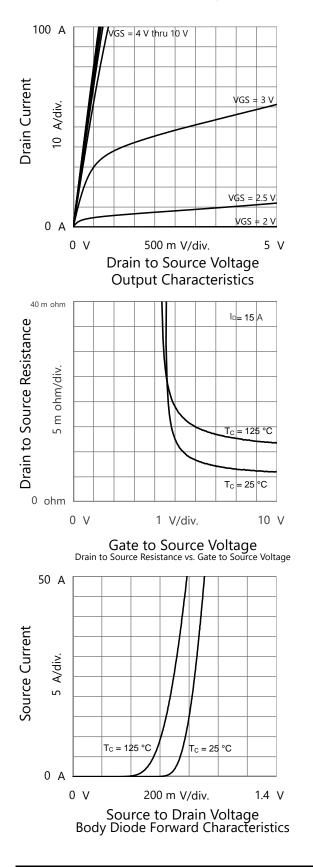
b. Guaranteed by design, not subject to production testing.

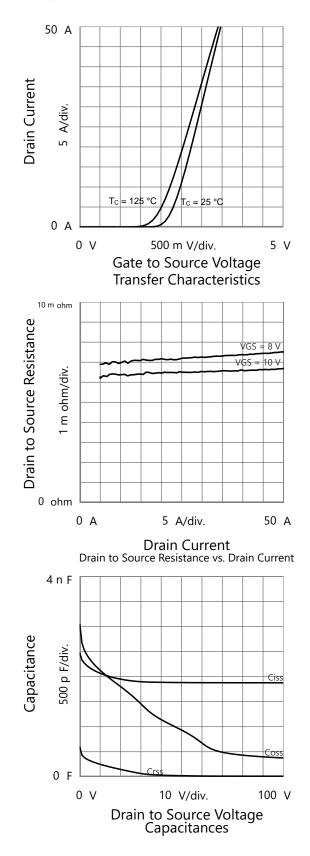
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

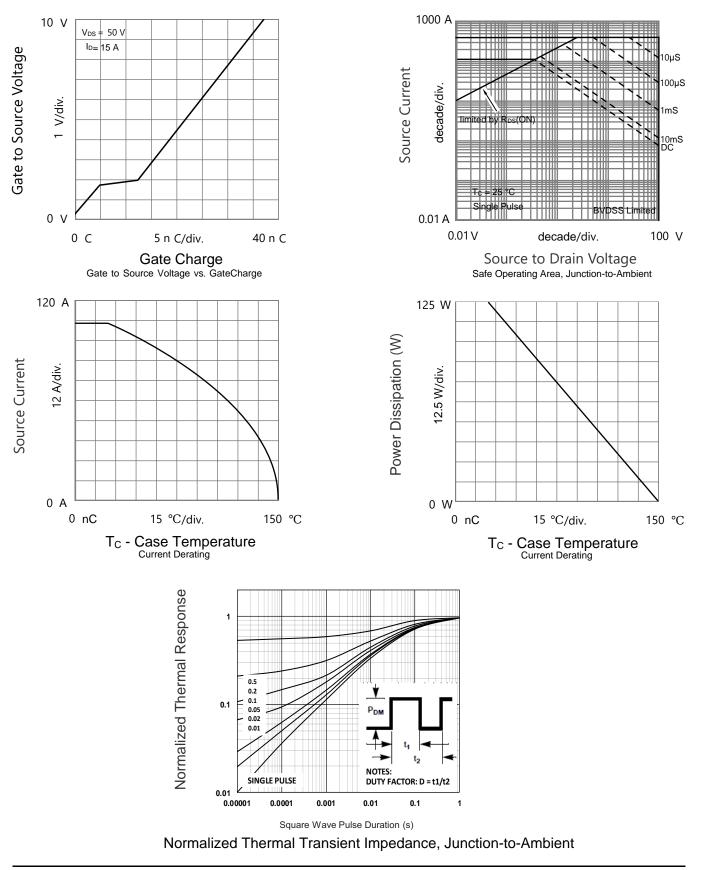






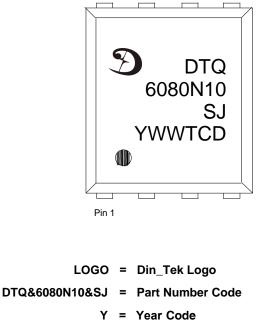
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





Mark:



- WW = Week Code
- TCD = Tracking Code

NOTES:

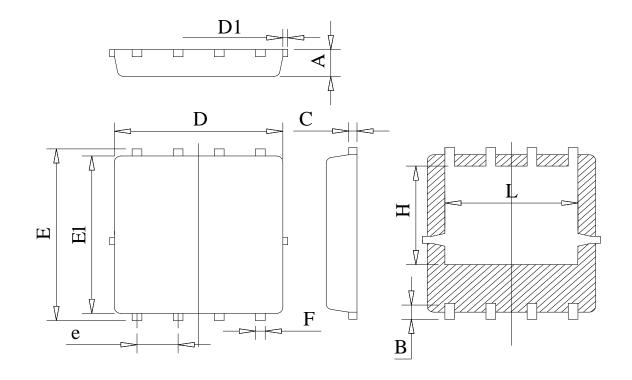
- Year Code : M = 2022, N = 2023, P = 2024, ... The easily confused letter "O" does not participate in sorting
- 2. Week Code : Week1 = 01, Week2 = 02, Week3 = 03, \dots

The current marking strategy is reflected. Contact your local sales representative for historical marking strategies for hese packages.



DFN5*6-8L PACKAGE OUTLINE

Din-Tek SEMICONDUCTOR



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit : mm			
Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
E	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25



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